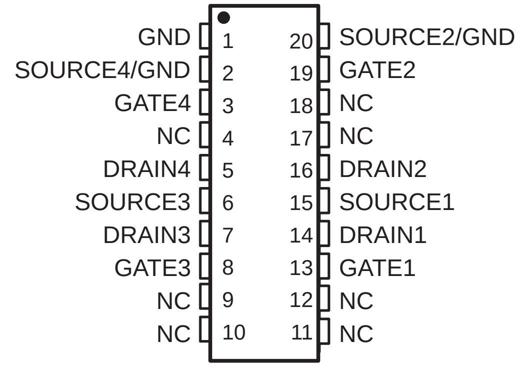
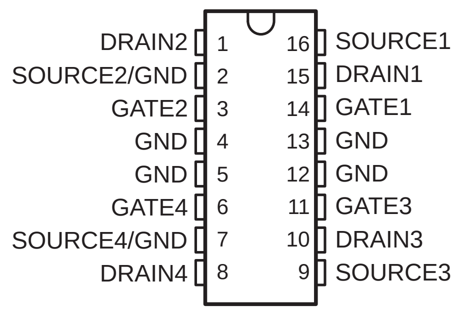
- **Low $r_{DS(on)}$ . . . 0.4 Ω Typ**
- **High-Voltage Output . . . 60 V**
- **Pulsed Current . . . 3 A Per Channel**
- **Fast Commutation Speed**
- **Direct Logic-Level Interface**

DW PACKAGE
(TOP VIEW)



NC – No internal connection

NE PACKAGE
(TOP VIEW)

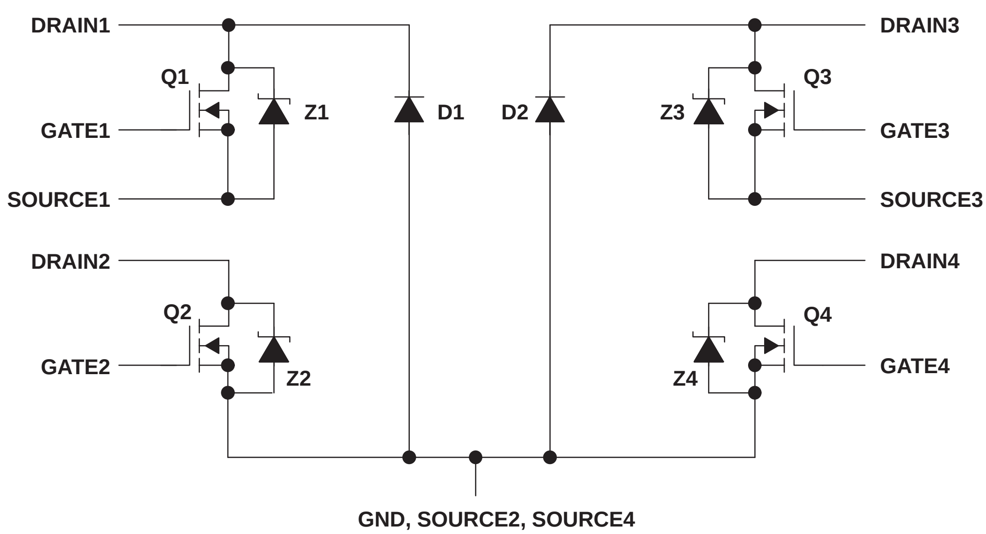


description

The TPIC5424L is a monolithic logic-level power DMOS array that consists of four electrically isolated N-channel enhancement-mode DMOS transistors, two of which are configured with a common source.

The TPIC5424L is offered in a 16-pin thermally enhanced dual-in-line (NE) package and a 20-pin wide-body surface-mount (DW) package. The TPIC5424L is characterized for operation over the case temperature range of –40°C to 125°C.

schematic



absolute maximum ratings over operating case temperature range (unless otherwise noted)†

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage (Q1, Q3)	100 V
Drain-to-GND voltage (Q1, Q3)	100 V
Drain-to-GND voltage (Q2, Q4)	60 V
Gate-to-source voltage, V_{GS}	±20 V
Continuous drain current, each output, T_C = 25°C	1 A
Continuous source-to-drain diode current, T_C = 25°C	1 A
Pulsed drain current, each output, I_{max}, T_C = 25°C (see Note 1 and Figure 15)	3 A
Single-pulse avalanche energy, E_{AS}, T_C = 25°C (see Figure 4)	180 mJ
Continuous total dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T_J	–40°C to 150°C
Operating case temperature range, T_C	–40°C to 125°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms and duty cycle = 2%.

DISSIPATION RATING TABLE

PACKAGE	$T_C \le$ 25°C POWER RATING	DERATING FACTOR ABOVE T_C = 25°C	T_C = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	279 mW
NE	2075 mW	16.6 mW/°C	415 mW

electrical characteristics, T_C = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	I_D = 250 µA, V_{GS} = 0		60			V
$V_{GS(th)}$	Gate-to-source threshold voltage	I_D = 1 mA, V_{DS} = V_{GS}, See Figure 5		1.5	1.85	2.2	V
$V_{(BR)}$	Reverse drain-to-GND breakdown voltage (across D1, D2)	Drain-to-GND current = 250 µA		100			V
$V_{DS(on)}$	Drain-to-source on-state voltage	I_D = 1 A, V_{GS} = 5 V, See Notes 2 and 3			0.4	0.48	V
$V_{F(SD)}$	Forward on-state voltage, source-to-drain	I_S = 1 A, V_{GS} = 0 (Z1, Z2, Z3, Z4), See Notes 2 and 3 and Figure 12			1	1.2	V
V_F	Forward on-state voltage, GND-to-drain	I_D = 1 A (D1, D2), See Notes 2 and 3			4.6		V
I_{DSS}	Zero-gate-voltage drain current	V_{DS} = 48 V, V_{GS} = 0	T_C = 25°C		0.05	1	µA
			T_C = 125°C		0.5	10	
I_{GSSF}	Forward gate current, drain short circuited to source	V_{GS} = 5 V, V_{DS} = 0			10	100	nA
I_{GSSR}	Reverse gate current, drain short circuited to source	V_{SG} = 5 V, V_{DS} = 0			10	100	nA
I_{lkg}	Leakage current, drain-to-GND	V_{DGND} = 48 V (D1, D2)	T_C = 25°C		0.05	1	µA
			T_C = 125°C		0.5	10	
$r_{DS(on)}$	Static drain-to-source on-state resistance	V_{GS} = 5 V, I_D = 1 A, See Notes 2 and 3 and Figures 6 and 7	T_C = 25°C		0.4	0.48	Ω
			T_C = 125°C		0.65	0.68	
g_{fs}	Forward transconductance	V_{DS} = 15 V, I_D = 0.5 A, See Notes 2 and 3 and Figure 9		1.25	1.39		S
C_{iss}	Short-circuit input capacitance, common source	V_{DS} = 25 V, V_{GS} = 0, f = 1 MHz, See Figure 11			220	275	pF
C_{oss}	Short-circuit output capacitance, common source				120	150	
C_{rss}	Short-circuit reverse-transfer capacitance, common source				100	125	

NOTES: 2. Technique should limit T_J – T_C to 10°C maximum.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain and GND-to-drain diode characteristics, T_C = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{rr}	Reverse-recovery time	I_S =0.5 A, V_{DS} = 48 V, V_{GS} = 0, di/dt = 100 A/µs, See Figures 1 and 14	Z1 and Z3		55		ns
			Z2 and Z4		150		
			D1 and D2		200		
Q_{RR}	Total diode charge		Z1 and Z3		0.06		µC
			Z2 and Z4		0.3		
			D1 and D2		0.7		

resistive-load switching characteristics, T_C = 25°C

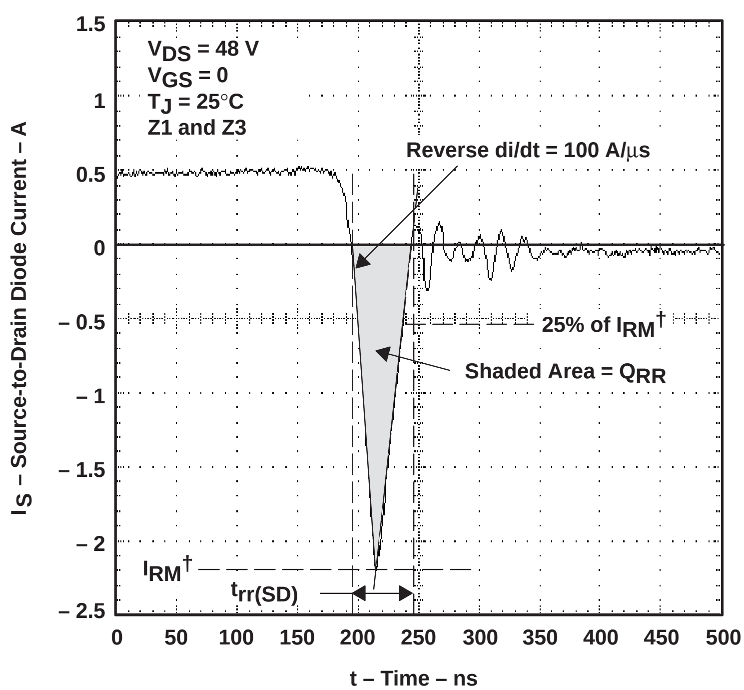
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$	Turn-on delay time	V_{DD} = 25 V, R_L = 25 Ω, t_{en} = 10 ns, t_{dis} = 10 ns, See Figure 2		34	68	ns
$t_{d(off)}$	Turn-off delay time			40	82	
t_r	Rise time			21	42	
t_f	Fall time			25	50	
Q_g	Total gate charge	V_{DS} = 48 V, I_D = 1 A, V_{GS} = 10 V, See Figure 3		3.9	5	nC
$Q_{gs(th)}$	Threshold gate-to-source charge			0.55	0.8	
Q_{gd}	Gate-to-drain charge			2.5	3.6	
L_D	Internal drain inductance			5		nH
L_S	Internal source inductance			5		
R_g	Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance (see Note 4)	DW package	All outputs with equal power		90		°C/W
		NE package			60		
$R_{\theta JP}$	Junction-to-pin thermal resistance	DW package			30		°C/W
		NE package			25		

NOTE 4: Package mounted on an FR4 printed-circuit board with no heat sink

PARAMETER MEASUREMENT INFORMATION

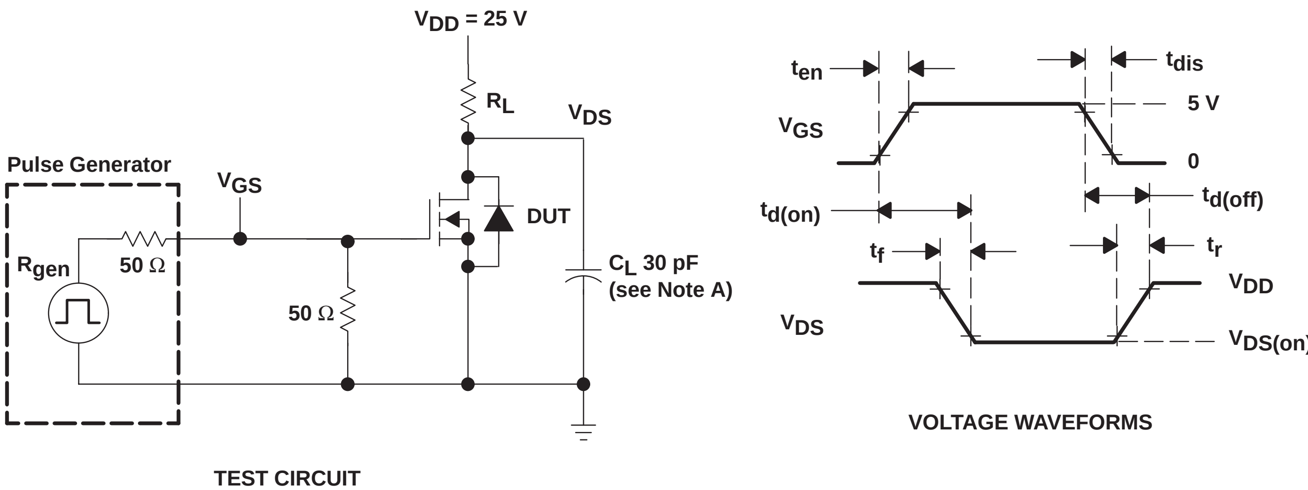


† I_{RM} = maximum recovery current

NOTE A. The above waveform is representative of Z2, Z4, D1, and D2 in shape only.

Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes probe and jig capacitance.

Figure 2. Resistive-Switching Test Circuit and Voltage Waveforms

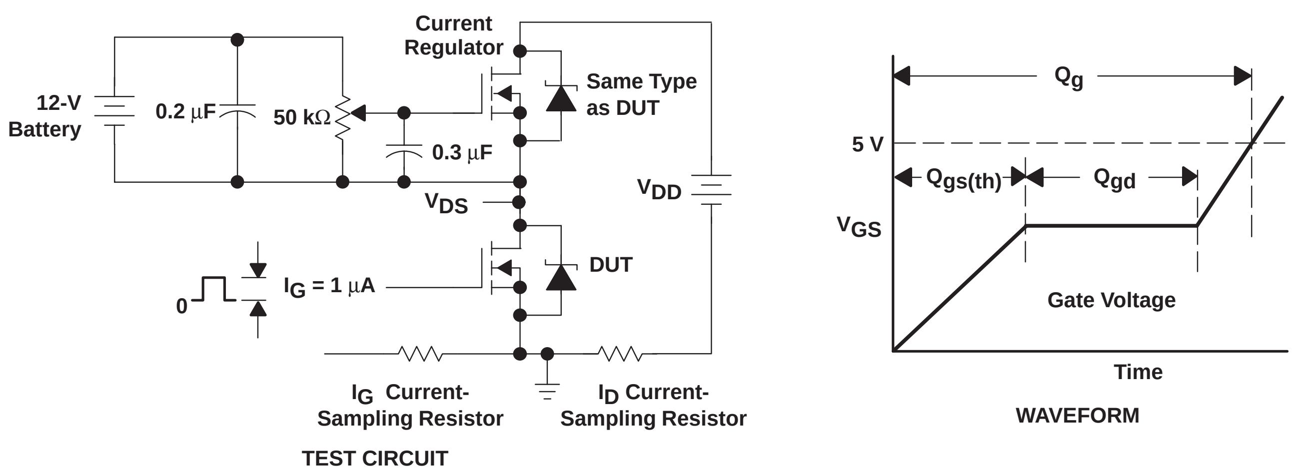
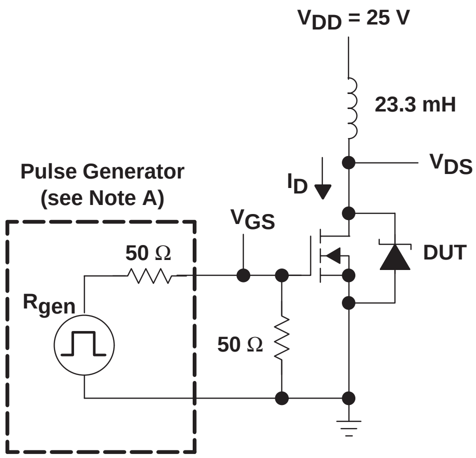
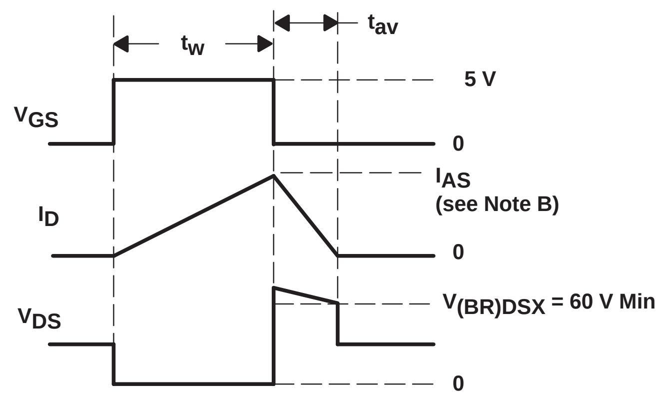


Figure 3. Gate-Charge Test Circuit and Waveform

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50\ \Omega$.
B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 3$ A.

Energy test level is defined as $E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 180$ mJ.

Figure 4. Single-Pulse Avalanche-Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

GATE-TO-SOURCE THRESHOLD VOLTAGE
vs
JUNCTION TEMPERATURE

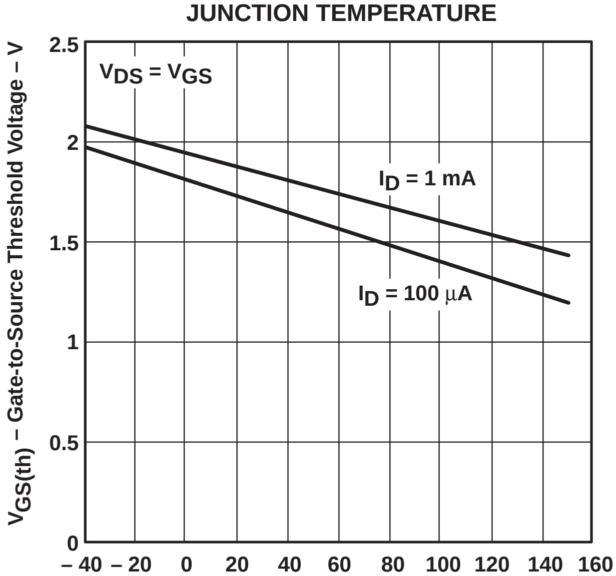


Figure 5

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
JUNCTION TEMPERATURE

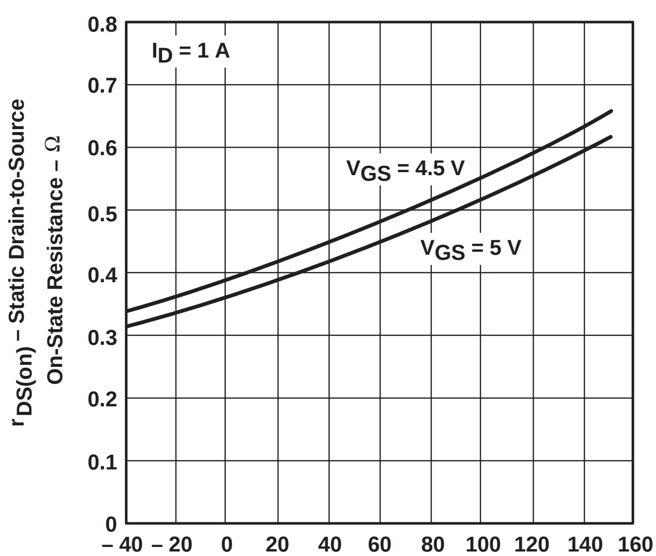


Figure 6

TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT

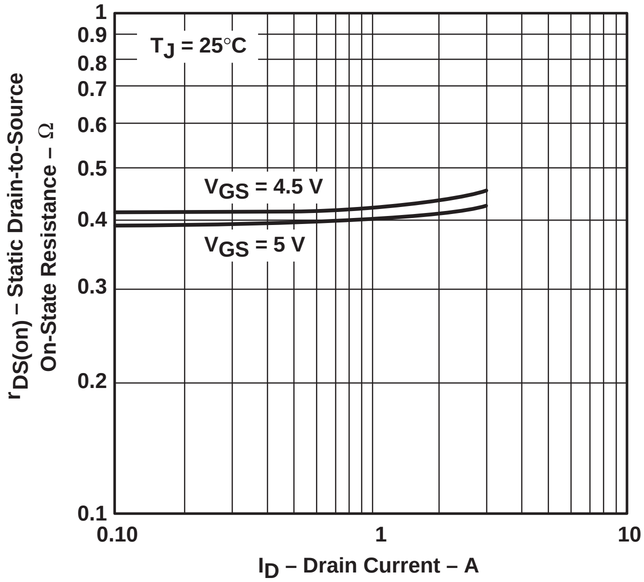


Figure 7

DRAIN CURRENT
vs
DRAIN-TO-SOURCE VOLTAGE

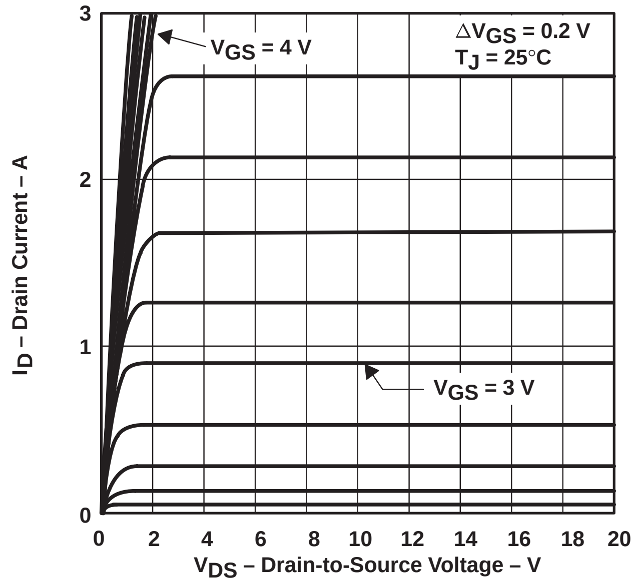


Figure 8

DISTRIBUTION OF
FORWARD TRANSCONDUCTANCE

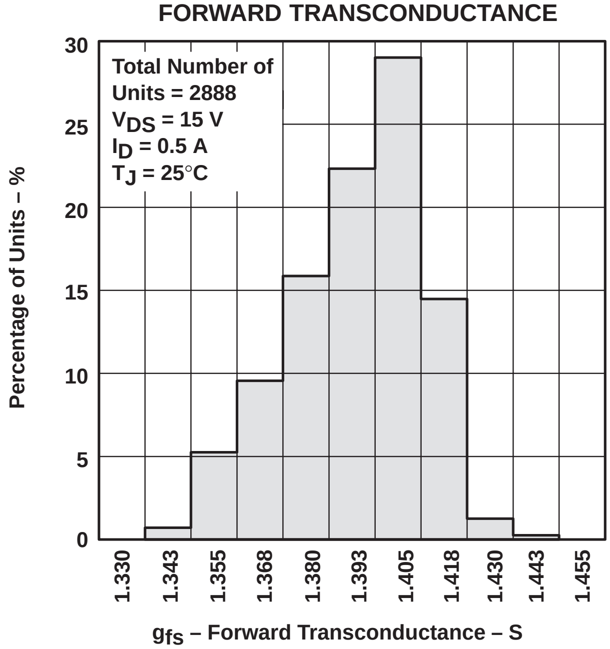


Figure 9

DRAIN CURRENT
vs
GATE-TO-SOURCE VOLTAGE

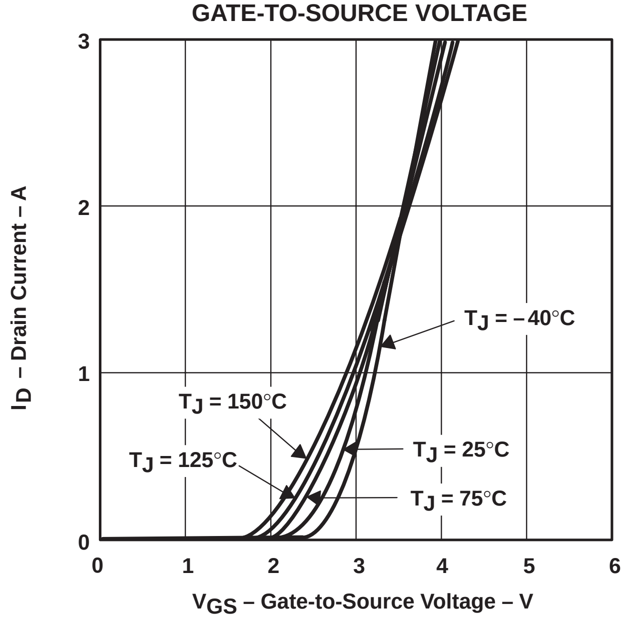


Figure 10

TYPICAL CHARACTERISTICS

CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

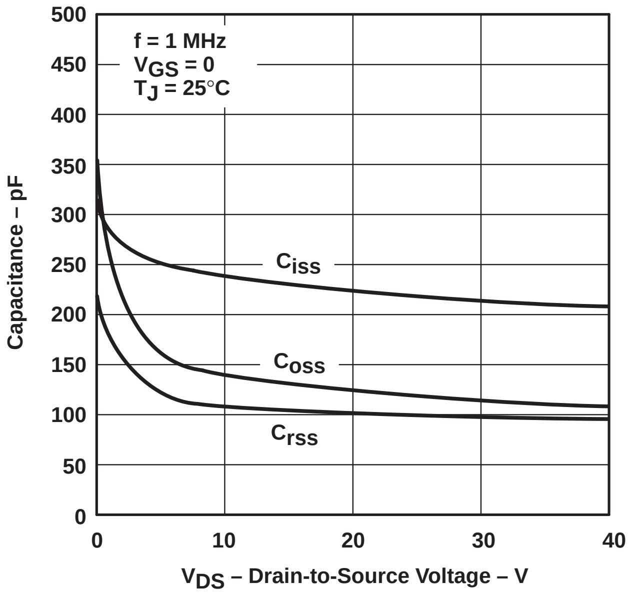


Figure 11

SOURCE-TO-DRAIN DIODE CURRENT vs SOURCE-TO-DRAIN VOLTAGE

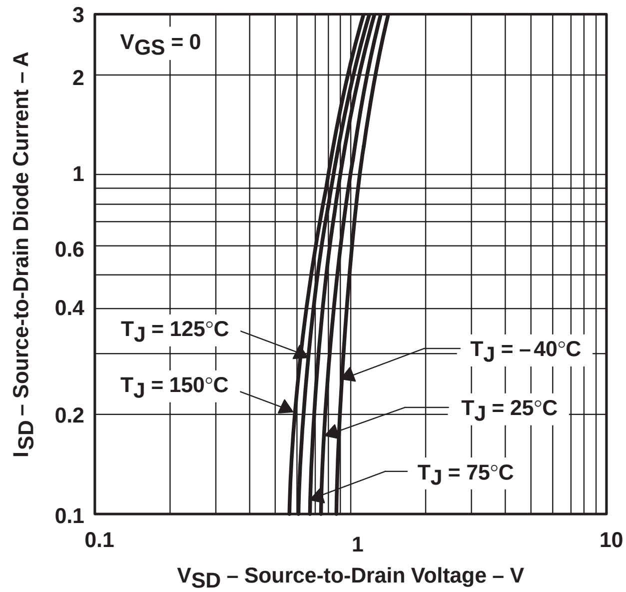


Figure 12

GATE-TO-SOURCE VOLTAGE vs GATE CHARGE

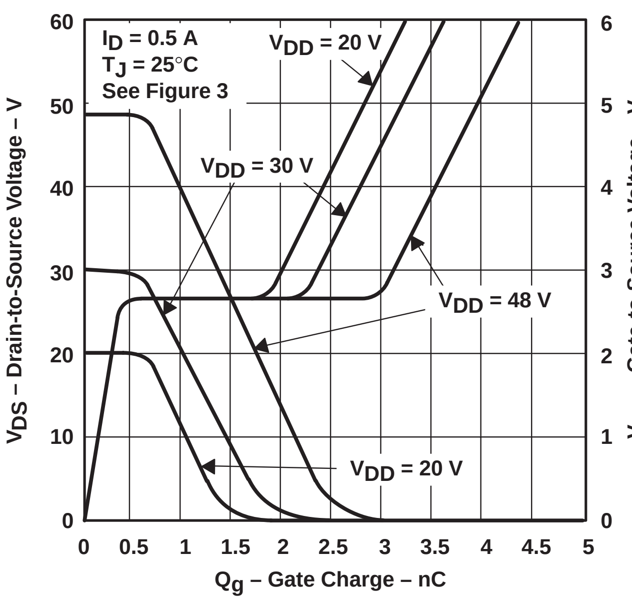


Figure 13

REVERSE-RECOVERY TIME vs REVERSE di/dt

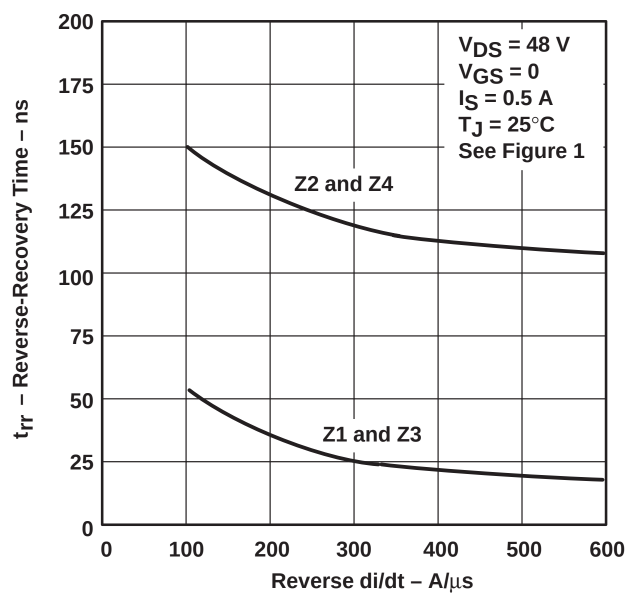
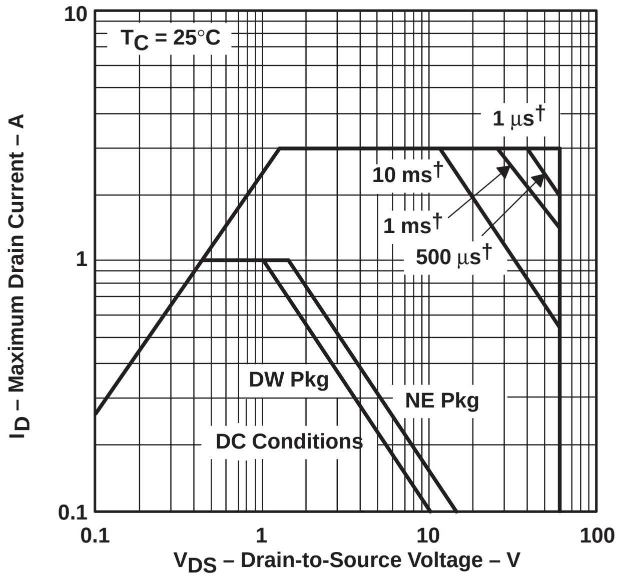


Figure 14

THERMAL INFORMATION

MAXIMUM DRAIN CURRENT vs DRAIN-TO-SOURCE VOLTAGE



† Less than 2% duty cycle

Figure 15

MAXIMUM PEAK-AVALANCHE CURRENT vs TIME DURATION OF AVALANCHE

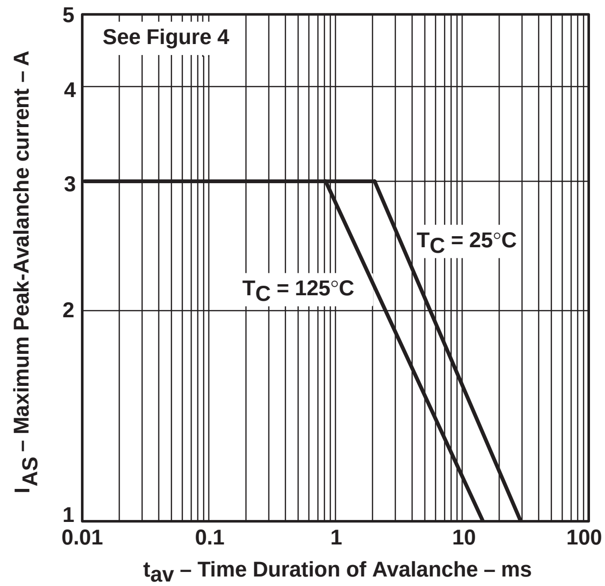
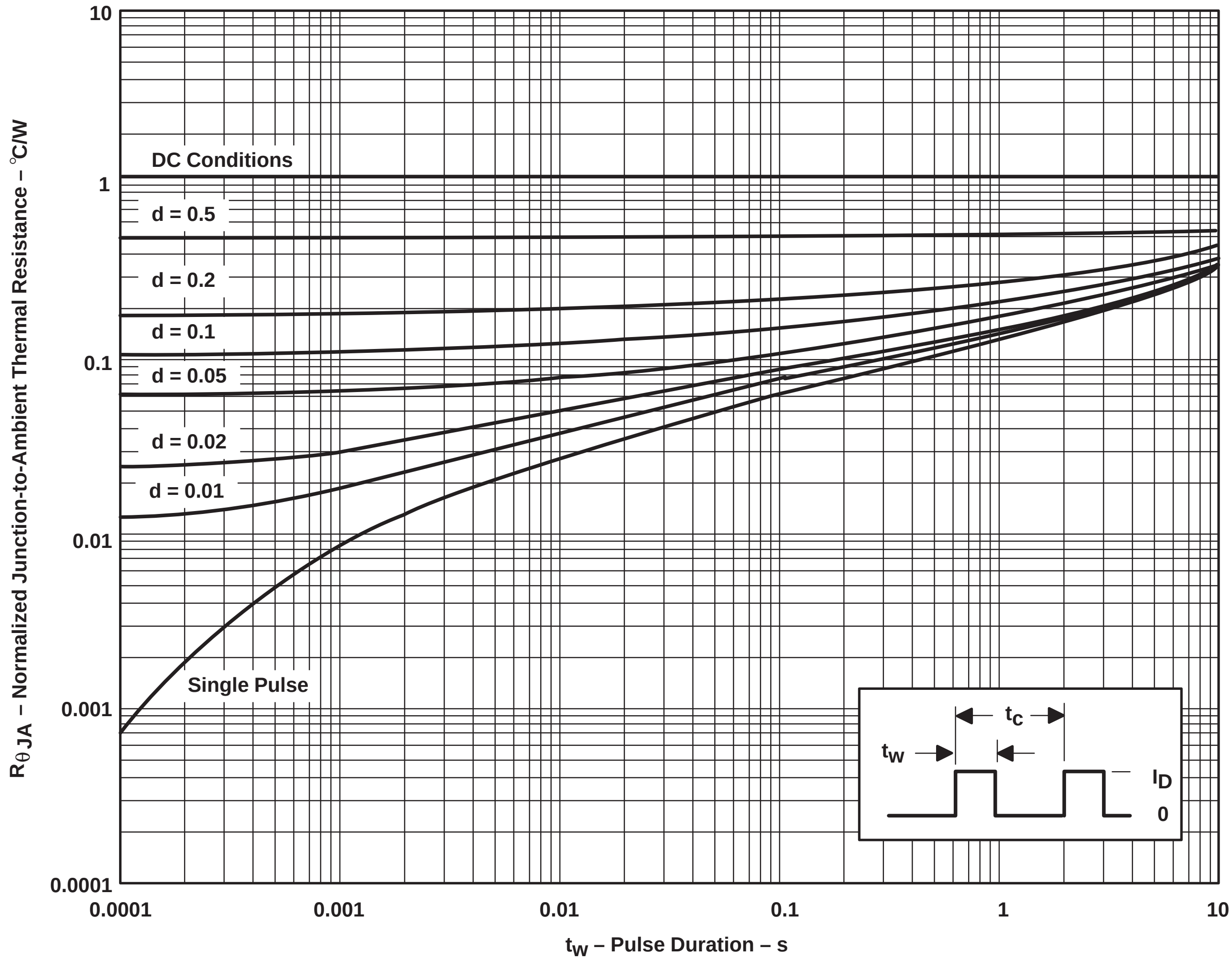


Figure 16

THERMAL INFORMATION

**NE PACKAGE†
NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE
vs
PULSE DURATION**



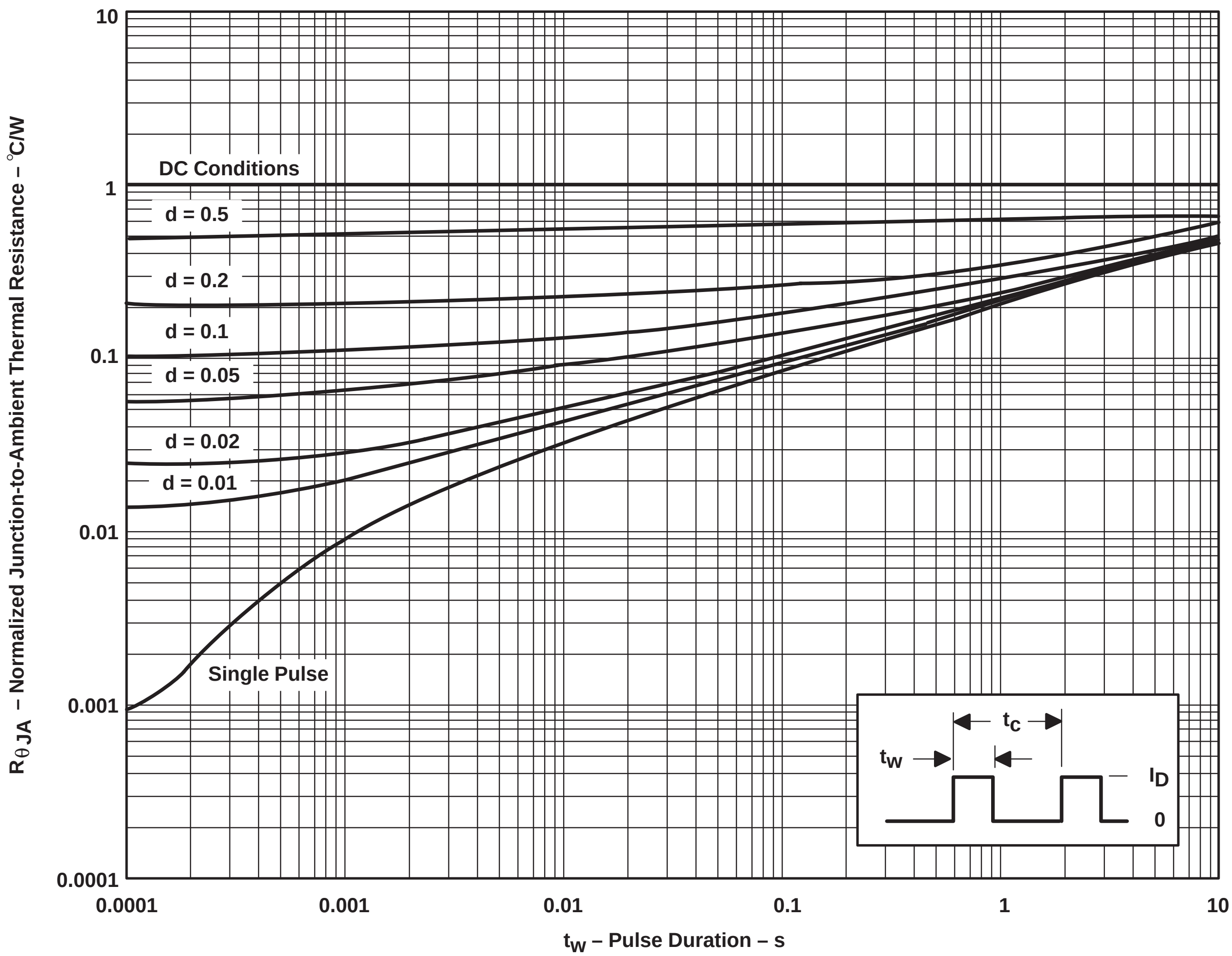
† Device mounted on FR4 printed-circuit board with no heat sink

NOTES: $Z_{\theta A}(t) = r(t)\ R_{\theta JA}$
t_W = pulse duration
t_C = cycle time
d = duty cycle = t_W/t_C

Figure 17

THERMAL INFORMATION

**DW PACKAGE†
NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE
vs
PULSE DURATION**



† Device mounted on FR4 printed-circuit board with no heat sink

NOTES: $Z_{\theta A}(t) = r(t)\ R_{\theta JA}$
t_W = pulse duration
t_C = cycle time
d = duty cycle = t_W/t_C

Figure 18

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